3.3 V octal D-type flip-flop; 3-state Rev. 7 — 22 November 2011

### 1. General description

The 74LVT574; 74LVTH574 is a high-performance product designed for  $V_{CC}$  operation at 3.3 V.

This device is an 8-bit, edge triggered register coupled to eight 3-state output buffers. The two sections of the device are controlled independently by the clock (pin CP) and output enable (pin  $\overline{OE}$ ) control gates. The state of each Dn input (one setup time before the LOW-to-HIGH clock transition) is transferred to the corresponding flip-flops Qn output.

The 3-state output buffers are designed to drive heavily loaded 3-state buses, MOS memories, or MOS microprocessors.

The active LOW output enable (pin  $\overline{OE}$ ) controls all eight 3-state buffers independent of the clock operation.

When pin OE is LOW, the stored data appears at the outputs. When pin OE is HIGH, the outputs are in the high-impedance OFF-state, which means they will neither drive nor load the bus.

### 2. Features and benefits

- Inputs and outputs arranged for easy interfacing to microprocessors
- 3-state outputs for bus interfacing
- Common output enable control
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Power-up reset
- Power-up 3-state
- Latch-up protection
  - JESD78 class II exceeds 500 mA
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Specified from –40 °C to +85 °C

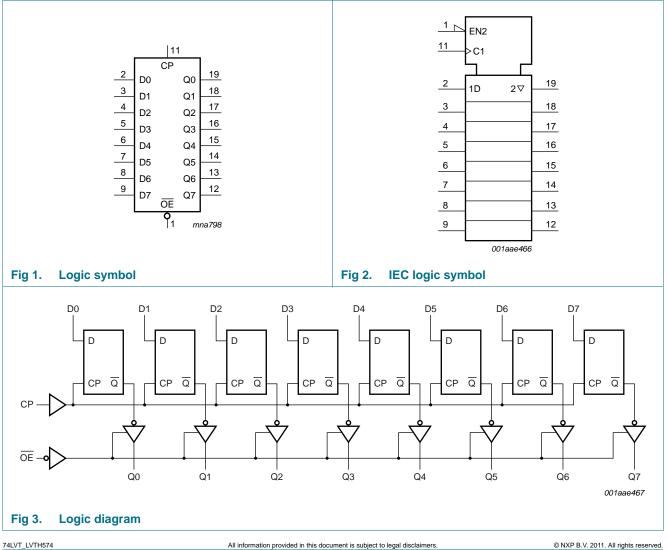


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# 3. Ordering information

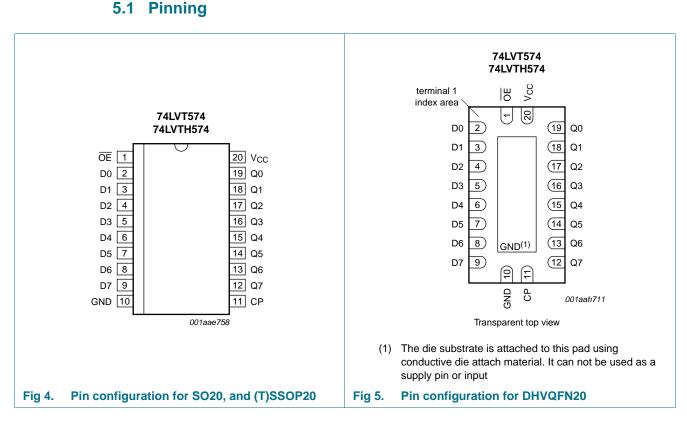
Type number	Package								
	Temperature range	Name	Description	Version					
74LVT574D	-40 °C to +85 °C SO20 plastic small outline package; 20 leads;		SOT163-1						
74LVTH574D			body width 7.5 mm						
74LVT574DB	–40 °C to +85 °C	SSOP20	plastic shrink small outline package; 20 leads;	SOT339-1					
74LVTH574DB			body width 5.3 mm						
74LVT574PW	–40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads;	SOT360-1					
74LVTH574PW			body width 4.4 mm						
74LVT574BQ	–40 °C to +85 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85$ mm	SOT764-1					

# 4. Functional diagram



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## 5. Pinning information



### 5.2 Pin description

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Table 2.	Pin description	
Symbol	Pin	Description
OE	1	output enable input (active LOW)
D0 to D7	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
CP	11	clock pulse input (active rising edge)
Q0 to Q7	19, 18, 17, 16, 15, 14, 13, 12	data output
V <sub>CC</sub>	20	supply voltage

.

### 6. Functional description

#### 6.1 Function table

#### Table 3.Function table [1]

Operating mode	Control		Input	Internal registe	r Output
	OE	СР	Dn		Qn
Load and read register	L	$\uparrow$	I	L	L
			h	Н	Н
Hold	L	NC	Х	NC	NC
Disable outputs	Н	L or H	Х	NC	Z
		$\uparrow$	Dn	Dn	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

 $\uparrow$  = LOW-to-HIGH clock transition;

h = HIGH voltage level one setup time prior to the LOW-to-HIGH clock transition;

I = LOW voltage level one setup time prior to the LOW-to-HIGH clock transition;

Z = high-impedance OFF-state;

NC = no change;

X = don't care.

## 7. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Мах	Unit
-		Conditions			
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
VI	input voltage		<u>[1]</u> –0.5	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V	-	-50	mA
Ι <sub>ΟΚ</sub>	output clamping current	V <sub>O</sub> < 0 V	-	-50	mA
lo	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-	-64	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		[2] _	150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +85 \ ^{\circ}C$	<u>[3]</u> _	500	mW

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

[3] For SO20 packages: above 70 °C derate linearly with 8 mW/K.
 For SSOP20 and TSSOP20 packages: above 60 °C derate linearly with 5.5 mW/K.
 For DHVQFN20 packages: above 60 °C derate linearly with 4.5 mW/K.

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## 8. Recommended operating conditions

Table 5.	Recommended operating cond	ecommended operating conditions			
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		2.7	3.6	V
VI	input voltage		0	5.5	V
V <sub>IH</sub>	HIGH-level input voltage		2.0	-	V
V <sub>IL</sub>	LOW-level input voltage		-	0.8	V
I <sub>OH</sub>	HIGH-level output current		-	-32	mA
I <sub>OL</sub>	LOW-level output current		-	32	mA
		current duty cycle $\leq 50$ %; $f_{i} \geq 1 \ kHz$	-	64	mA
T <sub>amb</sub>	ambient temperature	in free air	-40	+85	°C
$\Delta t / \Delta V$	input transition rise and fall rate	outputs enabled	-	10	ns/V

## 9. Static characteristics

#### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		T <sub>amb</sub> =	–40 °C to +	85 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	
V <sub>IK</sub>	input clamping voltage	$V_{CC} = 2.7 \text{ V}; \text{ I}_{IK} = -18 \text{ mA}$		-1.2	-0.9	-	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{CC}$ = 2.7 V to 3.6 V; $I_{OH}$ = $-100~\mu A$		$V_{CC}-0.2$	$V_{CC}-0.1$	-	V
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -8 \text{ mA}$		2.4	2.5	-	V
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OH} = -32 \text{ mA}$		2.0	2.2	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>CC</sub> = 2.7 V					
		I <sub>OL</sub> = 100 μA		-	0.1	0.2	V
		I <sub>OL</sub> = 24 mA		-	0.3	0.5	V
		V <sub>CC</sub> = 3.0 V					
		I <sub>OL</sub> = 16 mA		-	0.25	0.4	V
		I <sub>OL</sub> = 32 mA		-	0.3	0.5	V
		I <sub>OL</sub> = 64 mA		-	0.4	0.55	V
V <sub>OL(pu)</sub>	power-up LOW-level output voltage	$V_{CC}$ = 3.6 V; $I_O$ = 1 mA; $V_I$ = GND or $V_{CC}$	[2]	-	0.13	0.55	V
I <sub>I</sub>	input leakage current	all input pins; V <sub>CC</sub> = 0 V or 3.6 V; V <sub>I</sub> = 5.5 V		-	1	10	μA
		control pins; $V_{CC}$ = 3.6 V; $V_{I}$ = $V_{CC}$ or GND		-	±0.1	±1	μA
		data pins; $V_{CC} = 3.6 V$	[3]				
		$V_I = V_{CC}$		-	0.1	1	μA
		$V_{I} = 0 V$		-5	-1	-	μA
I <sub>OFF</sub>	power-off leakage current	$V_{CC} = 0$ V; V <sub>I</sub> or V <sub>O</sub> = 0 V to 4.5 V		-	1	±100	μA
I <sub>LO</sub>	output leakage current	$V_{O}$ = 5.5 V and $V_{CC}$ = 3.0 V; output HIGH	[4]	-	60	125	μA
I <sub>BHL</sub>	bus hold LOW current	$V_{CC} = 3.0 \text{ V}; \text{ V}_{I} = 0.8 \text{ V}$		75	150	-	μA
I <sub>BHH</sub>	bus hold HIGH current	$V_{CC} = 3.0 \text{ V}; \text{ V}_{I} = 2.0 \text{ V}$	[4]	-	-150	-75	μA
I <sub>BHHO</sub>	bus hold HIGH overdrive current	$V_{CC} = 3.6 \text{ V}; \ V_I = 0 \text{ V} \text{ to } 3.6 \text{ V}$	<u>[4]</u>	-	-	500	μΑ

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Symbol	Parameter	Conditions		T <sub>amb</sub> = –40 °C to +85 °C			Unit
			Min	Typ <mark>[1]</mark>	Мах		
I <sub>BHLO</sub>	bus hold LOW overdrive current	$V_{CC} = 3.6 \text{ V}; V_{I} = 0 \text{ V to } 3.6 \text{ V}$		-500	-	-	μA
I <sub>O(pu/pd)</sub>	power-up/power-down output current	$V_{CC} \le 1.2 \text{ V}; V_O = 0.5 \text{ V to } V_{CC};$ $V_I = GND \text{ or } V_{CC}; \overline{OE} = \text{don't care}$	<u>[5]</u>	-	1	±100	μA
l <sub>oz</sub>	OFF-state output current	$V_{CC}$ = 3.6 V; $V_{I}$ = $V_{IH}$ or $V_{IL}$					
		output HIGH: V <sub>O</sub> = 3.0 V		-	1	5	μA
		output LOW: $V_0 = 0.5 V$		-5	1	-	μΑ
I <sub>CC</sub>	supply current	$V_{CC}$ = 3.6 V; $V_{I}$ = GND or $V_{CC};I_{O}$ = 0 A					
		outputs HIGH		-	0.13	0.19	mA
		outputs LOW		-	3	12	mA
		outputs disabled	[6]	-	0.13	0.19	mA
∆I <sub>CC</sub>	additional supply current	per input pin; V_{CC} = 3 V to 3.6 V; one input at V_{CC} – 0.6 V and other inputs at V_{CC} or GND	[7]	-	0.1	0.2	mA
Cı	input capacitance	V <sub>I</sub> = 0 V or 3.0 V		-	4	-	pF
Co	output capacitance	outputs disabled; $V_0 = 0 V \text{ or } 3.0 V$		-	8	-	рF

#### Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

[1] Typical values are measured at V<sub>CC</sub> = 3.3 V and T<sub>amb</sub> = 25 °C.

[2] For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.

[3] Unused pins at V<sub>CC</sub> or GND.

[4] This is the bus hold overdrive current required to force the input to the opposite logic state.

[5] This parameter is valid for any V<sub>CC</sub> between 0 V and 1.2 V with a transition time of up to 10 ms. From V<sub>CC</sub> = 1.2 V to V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V a transition time of 100  $\mu$ s is permitted. This parameter is valid for T<sub>amb</sub> = 25 °C only.

[6]  $I_{CC}$  is measured with outputs pulled to  $V_{CC}$  or GND.

[7] This is the increase in supply current for each input at the specified voltage level other than V<sub>CC</sub> or GND.

### **10.** Dynamic characteristics

#### Table 7.Dynamic characteristics

Voltages are referenced to ground (GND = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions	T <sub>amb</sub> = -	T <sub>amb</sub> = -40 °C to +85 °C			
			Min	Typ <mark>[1]</mark>	Max		
t <sub>PLH</sub>	LOW to HIGH propagation delay	CP to Qn; see <u>Table 6</u>					
	$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.7	3.6	5.4	ns		
		$V_{CC} = 2.7 V$	-	-	6.2	ns	
t <sub>PHL</sub> HIGH to LOW propagation delay		CP to Qn; see Table 6					
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.4	4.3	5.9	ns	
		$V_{CC} = 2.7 V$	-	-	6.6	ns	
t <sub>PZH</sub>	OFF-state to HIGH propagation delay	OE to Qn; see Figure 7					
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	2.9	4.8	ns	
		$V_{CC} = 2.7 V$	-	-	5.9	ns	

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Symbol	Parameter	Conditions		T <sub>amb</sub> =	–40 °C to	+85 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	
t <sub>PZL</sub>	OFF-state to LOW propagation delay	OE to Qn; see Figure 8					
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.3	3.4	5.1	ns
		$V_{CC} = 2.7 V$		-	-	6.2	ns
PHZ	HIGH to OFF-state propagation delay	OE to Qn; see Figure 7					
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.9	4.0	5.5	ns
		$V_{CC} = 2.7 V$		-	-	5.9	ns
t <sub>PLZ</sub> LOW to OFF-state propagation delay	OE to Qn; see Figure 8						
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.7	3.2	4.5	ns
		$V_{CC} = 2.7 V$		-	-	4.5	ns
su	set-up time	Dn to CP; see Figure 9	[2]				
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.0	-	-	ns
		$V_{CC} = 2.7 V$		2.4	-	-	ns
h	hold time	Dn to CP; see Figure 9	[3]				
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		0.3	-	-	ns
		$V_{CC} = 2.7 V$		0	-	-	ns
W	pulse width	CP input; see Figure 6	[4]				
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		3.3	-	-	ns
		$V_{CC} = 2.7 V$		3.3	-	-	ns
max	maximum frequency	CP input; $V_{CC} = 3.0$ V to 3.6 V; see Figure 6		150	-	-	MHz

#### Table 7 Dynamic characteristics continued

[1] Typical values are at V<sub>CC</sub> = 3.3 V and T<sub>amb</sub> = 25 °C.

 $[3] \quad t_h \, is \, the \, same \, as \, t_{h(H)} \, and \, t_{h(L)}$ 

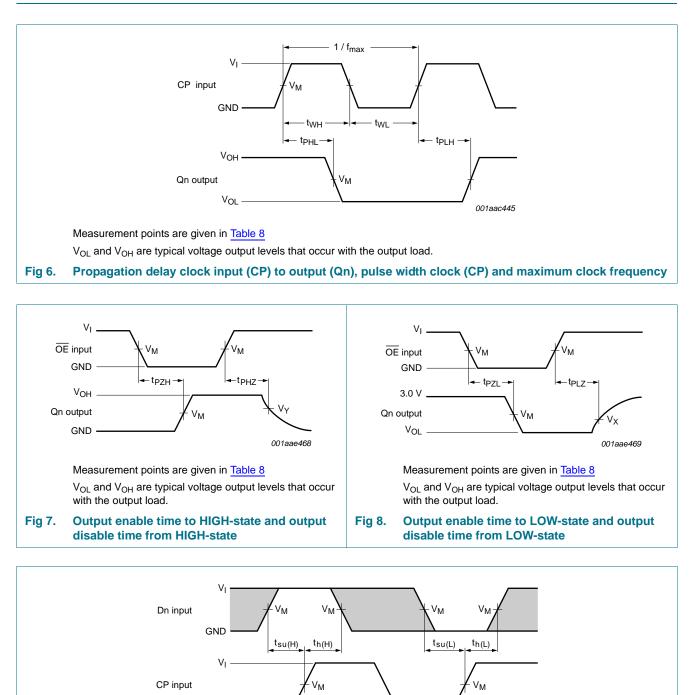
[4]  $t_W$  is the same as  $t_{WH}$  and  $t_{WL}$ 

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### 11. Waveforms



Measurement points are given in Table 8

GND

Remark: The shaded areas indicate when the input is permitted to change for predictable output performance.

Fig 9. Data setup and hold times

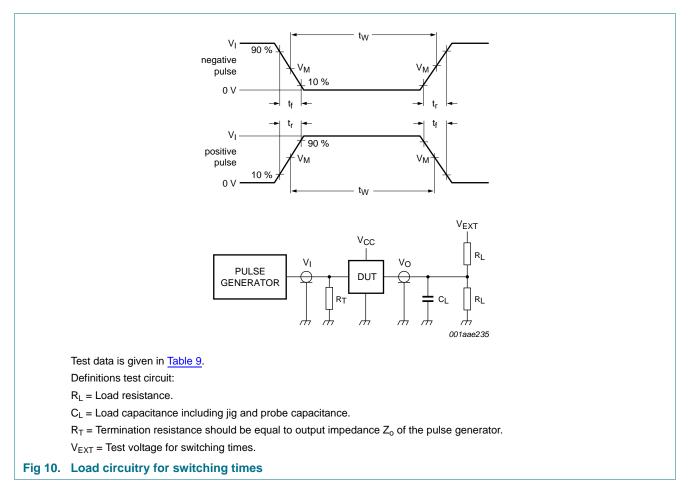
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#### **NXP Semiconductors**

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Table 8.	Measurement points						
Input		Output					
V <sub>M</sub>		V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>			
1.5 V		1.5 V	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> – 0.3 V			



#### Table 9. Test data

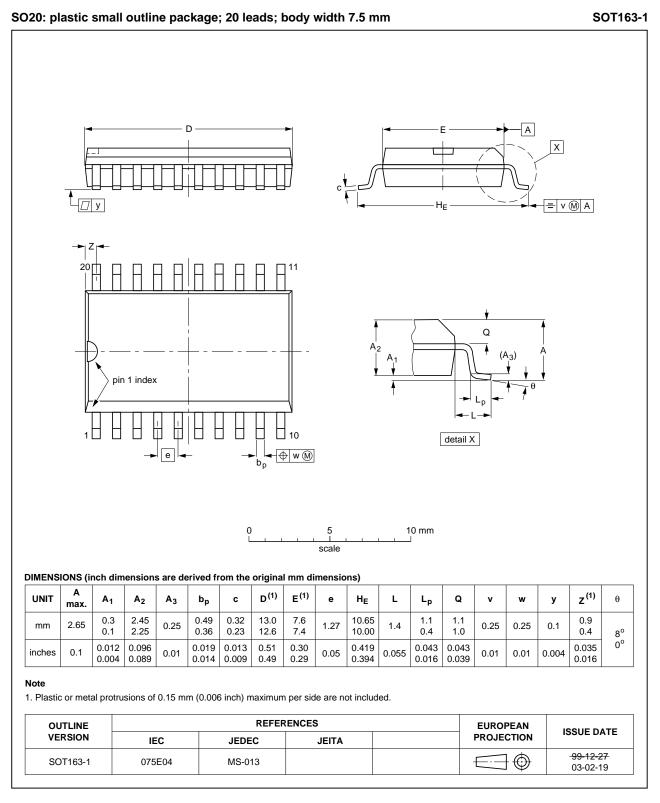
Input		Load		V <sub>EXT</sub>				
VI	f <sub>i</sub>	t <sub>W</sub>	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PHZ</sub> , t <sub>PZH</sub>	t <sub>PLZ</sub> , t <sub>PZL</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>
2.7 V	$\leq$ 10 MHz	500 ns	$\leq$ 2.5 ns	50 pF	500 Ω	GND	6 V	open

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### 12. Package outline



#### Fig 11. Package outline SOT163-1 (SO20)

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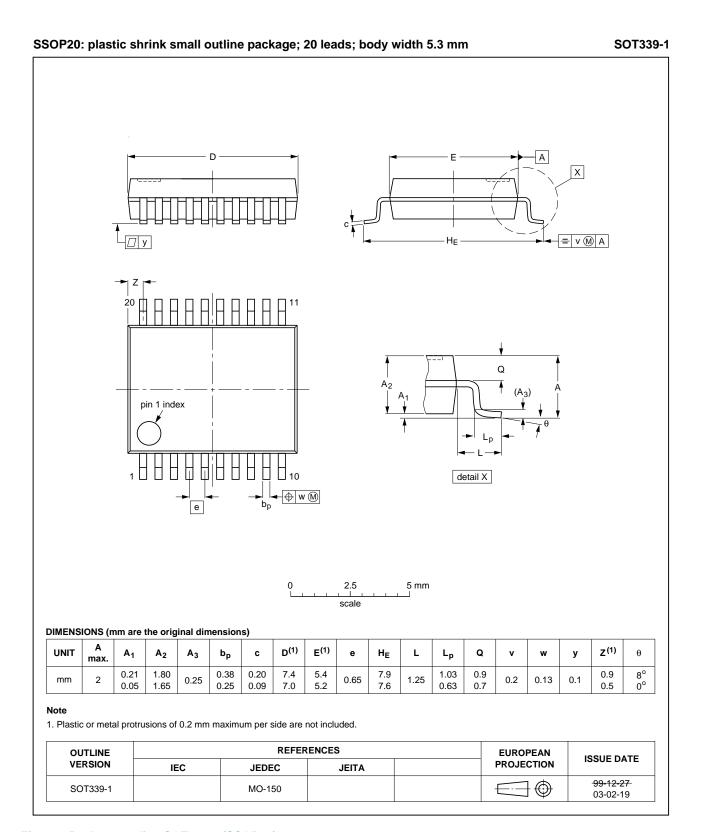
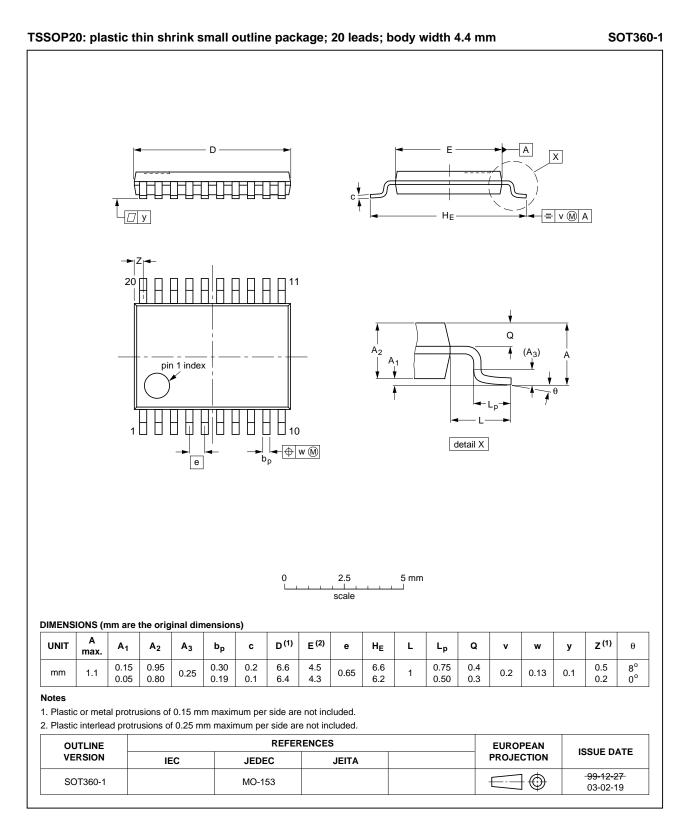


Fig 12. Package outline SOT339-1 (SSOP20)

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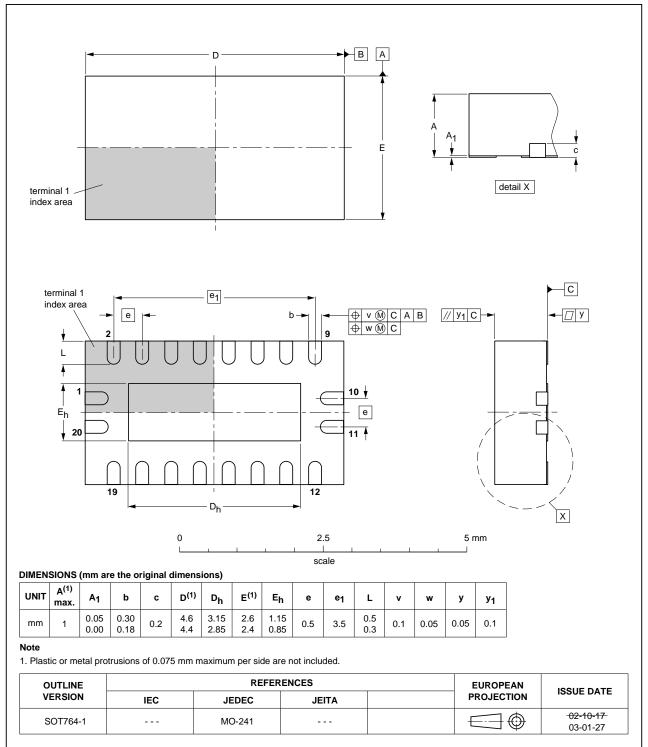
3.3 V octal D-type flip-flop; 3-state



#### Fig 13. Package outline SOT360-1 (TSSOP20)

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#### DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm SOT764-1

Fig 14. Package outline SOT764-1 (DHVQFN20)



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## **13. Abbreviations**

Table 10.	Abbreviations
Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
MOS	Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic

## 14. Revision history

Table 11. Revision histo	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVT_LVTH574 v.7	20111122	Product data sheet	-	74LVT_LVTH574 v.6
Modifications:	<ul> <li>Legal pages</li> </ul>	updated.		
74LVT_LVTH574 v.6	20110912	Product data sheet	-	74LVT_LVTH574 v.5
74LVT_LVTH574 v.5	20110727	Product data sheet	-	74LVT_LVTH574 v.4
74LVT_LVTH574 v.4	20080911	Product data sheet	-	74LVT_LVTH574 v.3
74LVT_LVTH574 v.3	20060323	Product data sheet	-	74LVT574 v.2
74LVT574 v.2	19980219	product specification	-	74LVT574 v.1
74LVT574 v.1	19951114	product specification	-	-

### 15. Legal information

### 15.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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#### 3.3 V octal D-type flip-flop; 3-state

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